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Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

Dated: June 7, 2002

By:   
Richard V. Burgujian  
*for* Reg. No. 31,744

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
[www.finnegan.com](http://www.finnegan.com)

Application Number: 09/559,757  
Filing Date: April 27, 2000  
Attorney Docket Number: 04329.2306



### APPENDIX TO AMENDMENT OF June 4, 2002

#### Version of Claim with Markings to Show Changes Made

#### AMENDMENTS TO THE CLAIM:

Please amend claim 1 as follows:

1. (Twice Amended) A semiconductor device comprising:  
a semiconductor substrate having a main plane in which a channel of a transistor is formed, the semiconductor substrate comprising a first region and a second region defined in a section taken along a direction of a channel length, the second region having a surface located lower than that of the first region, and the second region being connected to the first region;  
a gate insulating film formed on the first region and containing silicon, nitrogen and oxygen;  
a gate electrode formed on the gate insulating film, a lower edge of the gate electrode being in a round shape and containing silicon; and  
a post oxide film formed on the second region, containing silicon and oxygen and arranged to be in contact with the gate insulating film and the lower edge of the gate electrode [and the gate insulating film].

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FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com